

ABSTRACT OF THE INVENTION

5 The present invention is directed to a process for preparing single crystal silicon, in ingot or wafer form, wherein crucible rotation is utilized to control the average axial temperature gradient in the crystal, G_0 , as a function of radius (i.e., $G_0(r)$), particularly at or near the central axis. Additionally, crucible rotation modulation is utilized to obtain an axially uniform oxygen content therein.